



Micro Commercial Components
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S637T

Features

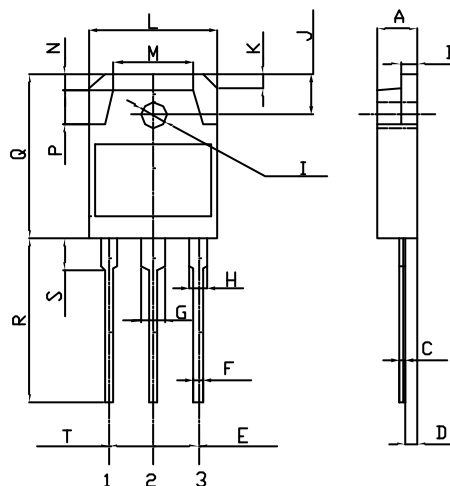
- With TO-3PN package
- Switching applications

NPN Silicon Power Transistors

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	400	V
V_{CBO}	Collector-Base Voltage	500	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current	15	A
P_C	Collector power dissipation	140	W
T_J	Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

TO-3PN



1. Base
2. Collector
3. Emitter

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=100\text{mA}$, $I_B=0$)	400	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=500\text{Vdc}$, $I_E=0$)	---	100	μAdc
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=5.0\text{Vdc}$, $I_C=0$)	---	20	mA

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer Ratio ($I_C=7.0\text{Adc}$, $V_{CE}=1.5\text{Vdc}$)	100	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=10\text{Adc}$, $I_B=1.5\text{Adc}$)	---	2.0	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=10\text{Adc}$, $I_B=1.5\text{Adc}$)	---	1.8	Vdc

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.181	.197	4.60	5.00	
B	.074	.083	1.90	2.10	
C	.022	.033	0.55	0.85	
D	.055		1.40		
E	.211	.219	5.35	5.55	
F	.037	.049	0.95	1.25	
G	.118		3.00		
H	.079		2.00		
I	.122	.130	3.10	3.30	
J	.189	.205	4.80	5.20	
K	.071		1.80		
L	.598	.630	15.20	16.00	
M	.378		9.6		
N	.079		2.0		
P	.157		4.0		
Q	.772	.795	19.6	20.2	
R	.787		20.0		
S	.157		4.0		
T	.211	.219	5.35	5.55	